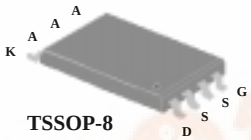
Advanced Power Electronics Corp.

P-CHANNEL WITH SCHOTTKY DIODE

POWER MOSFET

- ▼ Low On-Resistance
- ▼ Fast Switching Characteristic
- ▼ Included Schottky Diode

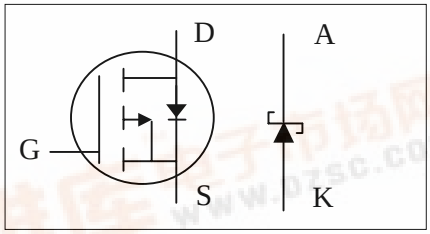


TSSOP-8

BV_{DSS}	-20V
$R_{DS(ON)}$	50mΩ
I_D	-3.5A

Description

The Advanced Power MOSFETs from APEC provide the designer with the best combination of fast switching, ruggedized device design, ultra low on-resistance and cost-effectiveness.



Absolute Maximum Ratings

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage (MOSFET and Schottky))	-20	V
V_{KA}	Reverse Voltage (Schottky)	20	V
V_{GS}	Gate-Source Voltage (MOSFET)	± 12	V
I_D@T_A=25℃	Continuous Drain Current[3] (MOSFET)	- 3.5	A
I_D@T_A=70℃	Continuous Drain Current[3] (MOSFET)	- 2.8	A
I_{DM}	Pulsed Drain Current[1] (MOSFET)	- 30	A
I_F	Average Forward Current (Schottky)	1	A
I_{FM}	Pulsed Forward Current[1] (Schottky)	25	A
P_D@T_A=25℃	Total Power Dissipation (MOSFET)	1	W
	Total Power Dissipation (Schottky)	1	W
T_{STG}	Storage Temperature Range	-55 to 150	℃
T_J	Operating Junction Temperature Range	-55 to 125	℃

Thermal Data

Symbol	Parameter		Value	Unit
Rthj-a	Thermal Resistance Junction-ambient[3] (MOSFET)	Max.	125	℃/W
	Thermal Resistance Junction-ambient[3] (Schottky)	Max.	125	℃/W

Electrical Characteristics@T_j=25°C(unless otherwise specified)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
BV_{DSS}	Drain-Source Breakdown Voltage	V_{GS}=0V, I_D=-250uA	-20	-	-	V
$\Delta BV_{DSS}/\Delta T_j$	Breakdown Voltage Temperature Coefficient	Reference to 25℃, I_D=-1mA	-	0.03	-	V/℃
$R_{DS(ON)}$	Static Drain-Source On-Resistance[2]	V_{GS}=-4.5V, I_D=-3.5A	-	-	50	mΩ
		V_{GS}=-2.5V, I_D=-2.7A	-	-	85	mΩ
$V_{GS(th)}$	Gate Threshold Voltage	V_{DS}=V_{GS}, I_D=-250uA	-0.5	-	-	V
g_{fs}	Forward Transconductance	V_{DS}=-10V, I_D=-3.5A	-	10	-	S
I_{DSS}	Drain-Source Leakage Current (T_j=25°C)	V_{DS}=-20V, V_{GS}=0V	-	-	1	uA
	Drain-Source Leakage Current (T_j=70°C)	V_{DS}=-16V ,V_{GS}=0V	-	-	25	uA
I_{GSS}	Gate-Source Leakage	V_{GS}= ± 12V	-	-	±100	nA
Q_g	Total Gate Charge[2]	I_D= -3.5A	-	15.6	-	nC
Q_{gs}	Gate-Source Charge	V_{DS}= -10V	-	2.1	-	nC
Q_{gd}	Gate-Drain ("Miller") Charge	V_{GS}= -4.5V	-	5.2	-	nC
$t_{d(on)}$	Turn-on Delay Time[2]	V_{DS}= -10V	-	8.2	-	ns
t_r	Rise Time	I_D= -1A	-	9.4	-	ns
$t_{d(off)}$	Turn-off Delay Time	R_G= 3.3Ω,V_{GS}= -4.5V	-	66.4	-	ns
t_f	Fall Time	R_D= 10Ω	-	48	-	ns
C_{iss}	Input Capacitance	V_{GS}=0V	-	660	-	pF
C_{oss}	Output Capacitance	V_{DS}=-20V	-	285	-	pF
C_{rss}	Reverse Transfer Capacitance	f=1.0MHz	-	130	-	pF

Source-Drain Diode

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
I_S	Continuous Source Current (Body Diode)	V_D=V_G=0V , V_S=-1.2V	-	-	-0.83	A
V_{SD}	Forward On Voltage[2]	I_S=-0.83A, V_{GS}=0V	-	-	-1.2	V

Schottky Characteristics@Tj=25℃

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
V_F	Forward Voltage Drop	I_F=1A	-	-	0.5	V
I_{rm}	Maximum Reverse Leakage Current	Vr=20V	-	-	100	uA

Notes:

1.Pulse width limited by Max. junction temperature.

2.Pulse width ≤300us , duty cycle ≤2%.

3.Surface mounted on 1 in^2 copper pad of FR4 board ; 208℃/W when mounted on Min. copper pad.

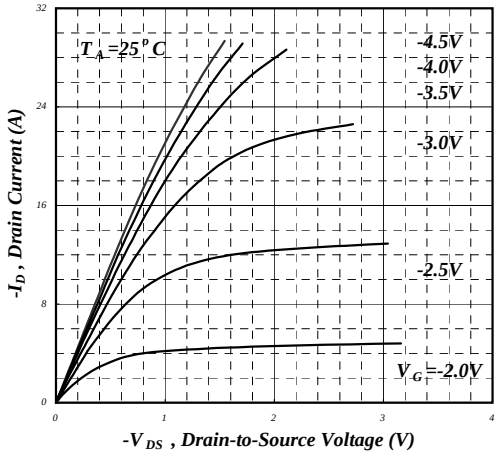


Fig 1. Typical Output Characteristics

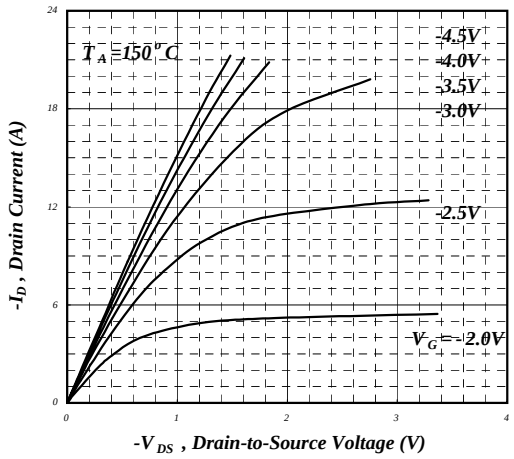


Fig 2. Typical Output Characteristics

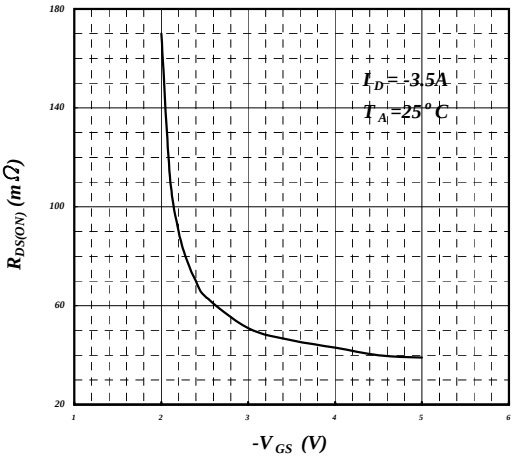


Fig 3. On-Resistance v.s. Gate Voltage

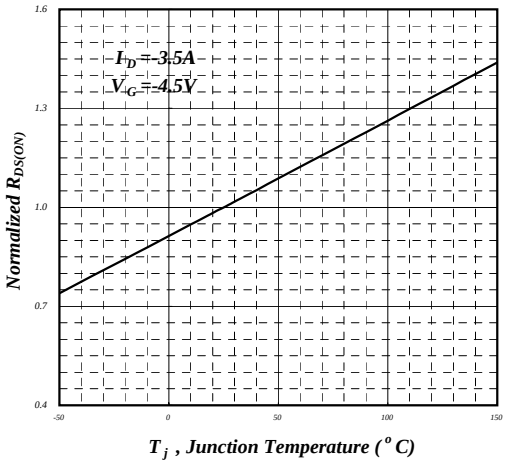


Fig 4. Normalized On-Resistance v.s. Junction Temperature

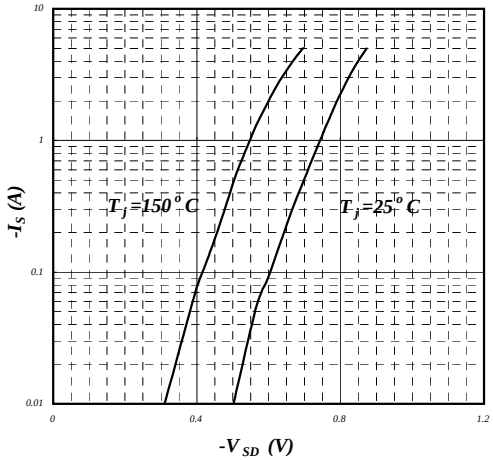


Fig 5. Forward Characteristic of Reverse Diode

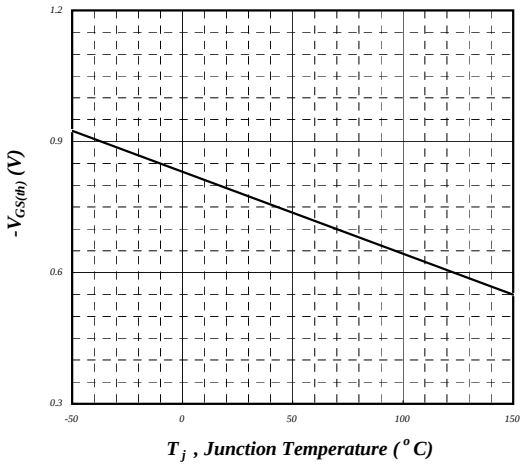


Fig 6. Gate Threshold Voltage v.s. Junction Temperature

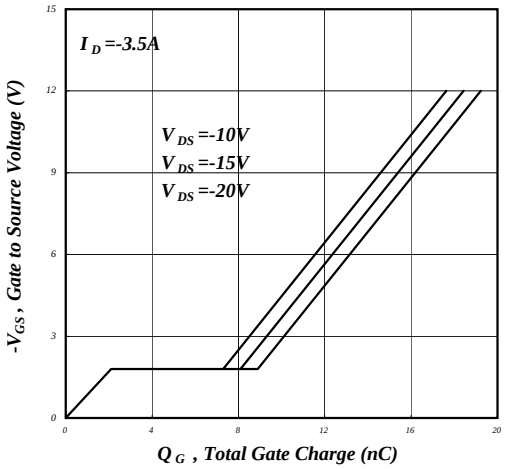


Fig 7. Gate Charge Characteristics

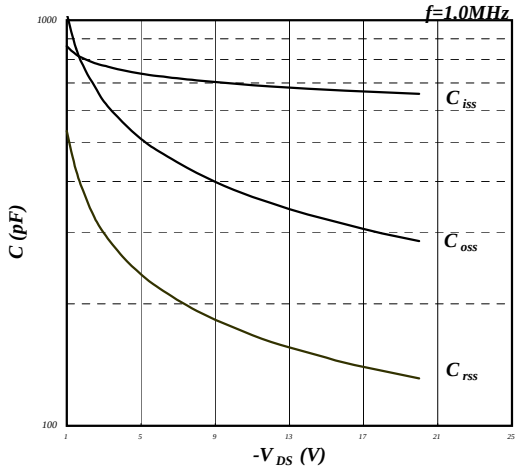


Fig 8. Typical Capacitance Characteristics

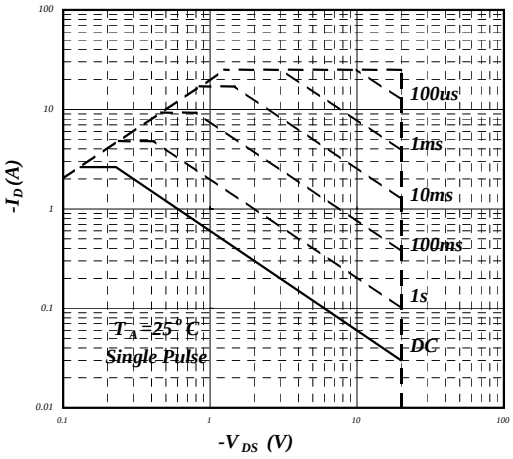


Fig 9. Maximum Safe Operating Area

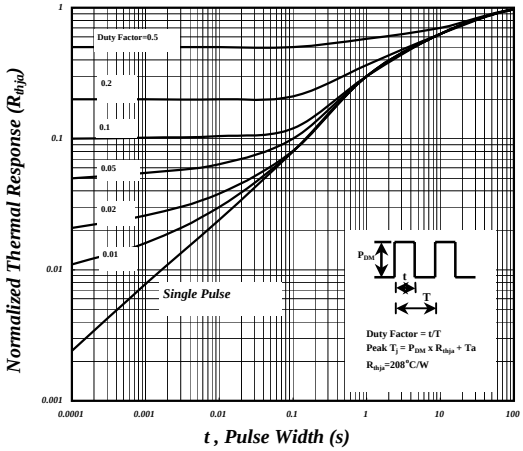


Fig 10. Effective Transient Thermal Impedance

SCHOTTKY DIODE

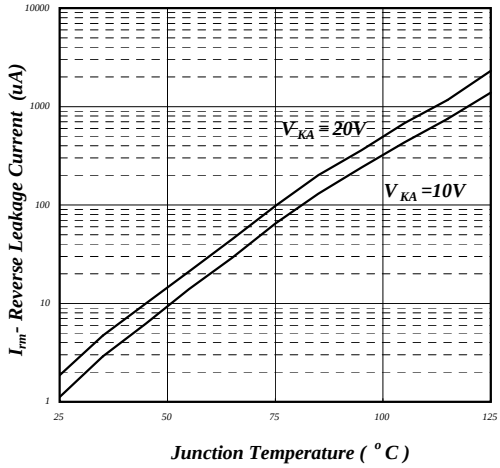


Fig 1. Reverse Leakage Current v.s. Junction Temperature

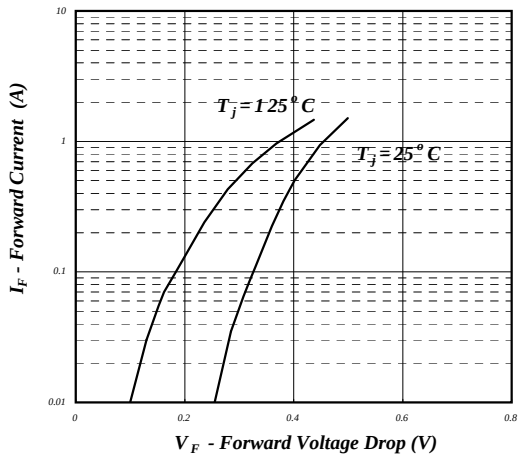


Fig 2. Forward Voltage Drop